

## Operational Amplifiers

### Noise Calculations of Instrumentation Amplifier Circuits

#### Abstract

Adding to the understanding of noise calculations from Application Note: Noise Calculations of Op-Amp Circuits, this application note describes calculating the output noise of an Instrumentation Amplifier (INA). As in the case of op-amps, the noise parameters from the device datasheet help determine the output noise of the classic three op-amp INA.

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# 1. Introduction

Instrumentation amplifiers amplify small input signals accurately. Because noise has a detrimental effect on small signals, it is important to understand the contributions of all noise sources involved. [Figure 1](#) shows the schematic of the classic three op-amp INA with its input source resistances. Because of the symmetry of the INA input stage, it is common to assign one half of the source resistance,  $R_S/2$ , to each INA input.

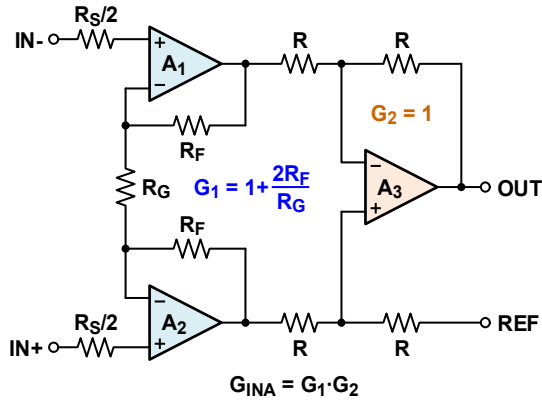


Figure 1. Driver with Drive Logic and H-Bridge Output

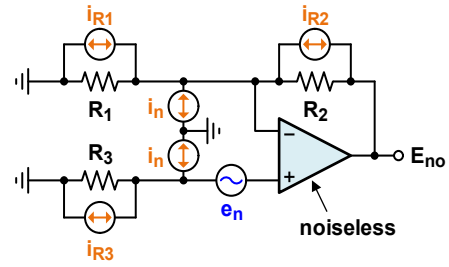


Figure 2. Driver Differential and Common-Mode Output Voltages

# 2. INA Noise Models

For a discrete INA design, it is possible to develop a detailed noise model by applying the standard op-amp noise model in [Figure 2](#) to each of the three amplifiers ([Figure 3](#)). The op-amp noise model uses noise currents of equal magnitude ( $i_{n+} = i_{n-} = i_n$ ) to accommodate the single noise current specifications in op-amp datasheets.

The resulting noise model is complex and its computation tedious.

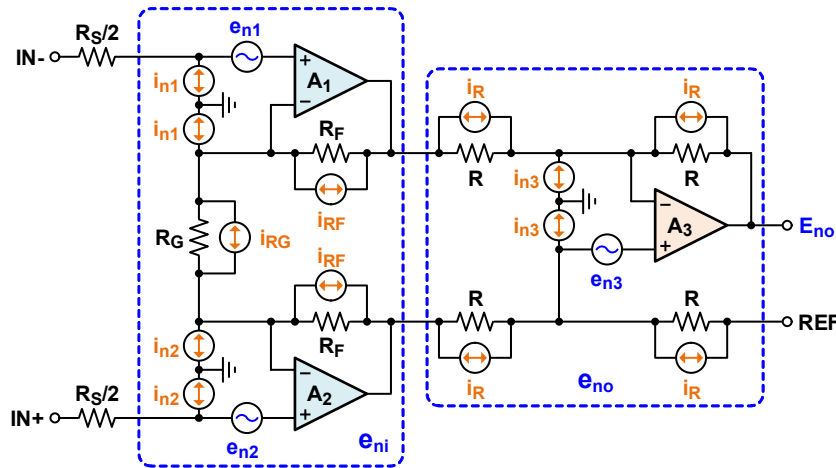


Figure 3. Detailed Noise Model of a Discrete 3-Amp INA

The noise models of integrated INAs are simpler. Some INA manufacturers model the noise of the input and output stages separately, which are indicated in [Figure 4](#) with the spectral densities,  $e_{ni}$  and  $e_{no}$ .

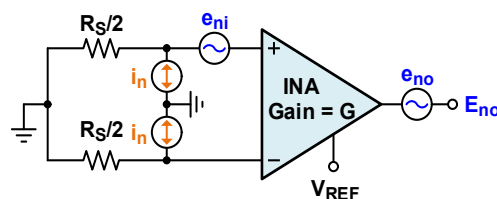


Figure 4. INA Noise Model with Separate Input and Output Voltage Noise Sources,  $e_{ni}$  and  $e_{no}$

Others model INA noise with a single input referred voltage noise,  $e_n$ , by dividing  $e_{no}$  by the INA gain and placing it in series with  $e_{ni}$ . The total input-referred voltage noise,  $e_n$ , then is the rms sum of  $e_{ni}$  and  $e_{no}$  (Figure 5):

$$(EQ. 1) \quad e_n = \sqrt{e_{ni}^2 + (e_{no}/G)^2}$$

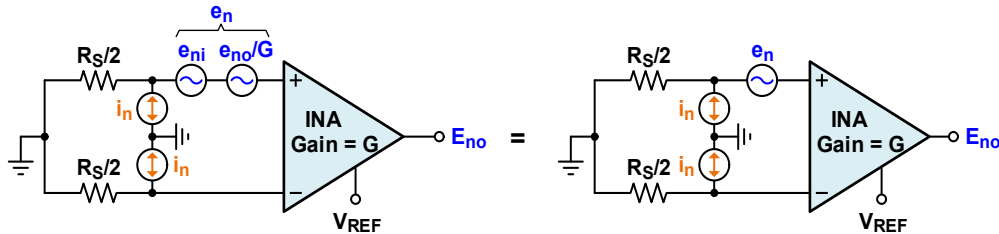


Figure 5. INA Noise Model with Total Input-referred (RTI) Voltage Noise,  $e_n$

In this model, the voltage source of the differential input stage,  $e_{ni}$ , and the voltage noise due to noise current,  $i_n \cdot R_S/2$ , are amplified by the INA gain. Both noise sources are uncorrelated and must be added quadratically to yield the total rms input noise of the INA:

$$(EQ. 2) \quad E_{ni(INA)} = \sqrt{NEB} \cdot \sqrt{e_{n(RTI)}^2 + 2 i_n^2 (R_S/2)^2}$$

where NEB is the noise equivalent bandwidth, calculated with  $NEB = 1.57 \times \text{INA Bandwidth (} f_{-3dB} \text{) at Gain = G}$ .

To determine the rms output noise of the INA,  $E_{ni(INA)}$  is multiplied by the INA gain:

$$(EQ. 3) \quad E_{no(INA)} = G \cdot E_{ni(INA)} = G \cdot \sqrt{NEB} \cdot \sqrt{e_{n(RTI)}^2 + 2 i_n^2 (R_S/2)^2}$$

Equation 2 and Equation 3 only provide the rms input and output noise of the INA. Neither the thermal noise from the source resistance,  $E_{no(Rs)}$ , nor the output noise of a reference buffer,  $E_{no(REF)}$ , are included. These noise sources add to the INA output noise,  $E_{no(INA)}$ , to yield the total rms noise of the INA circuit:

$$(EQ. 4) \quad E_{no} = \sqrt{E_{no(INA)}^2 + E_{no(Rs)}^2 + E_{no(REF)}^2}$$

### 3. Calculation Example

This example shows how to calculate the total output noise of the bridge-sensor signal-conditioner in Figure 6, using the instrumentation amplifier, ISL28534, at a gain of  $G = 100$ . The circuit is powered by a 5V single-supply and uses a 2.5V reference buffer to bias the INA output at mid-rail, when the bridge is in a balanced condition.

Figure 7 lists the parametric values of the circuit design for clarity. The values for the gain bandwidth products and the noise spectral densities are taken from the datasheet.

The closed-loop bandwidths of the INA and the OPA are calculated with  $f_{BW} = \text{GBWP}/\text{Gain}$ , which results in  $f_{BW(INA)} = 2.3\text{MHz}/100 = 23\text{kHz}$  and  $f_{BW(OPA)} = 3\text{MHz}/1 = 3\text{MHz}$ .

Because both closed-loop gains represent a 1st order low-pass, their noise equivalent bandwidths are calculated with  $NEB = 1.57 \cdot f_{BW}$ , therefore resulting in  $NEB_{INA} = 1.57 \cdot f_{BW(INA)} = 1.57 \cdot 23\text{kHz} = 36.1\text{kHz}$  and  $NEB_{OPA} = 1.57 \cdot f_{BW(OPA)} = 1.57 \cdot 3\text{MHz} = 4.71\text{MHz}$ .

The source resistance,  $R_S/2$ , for each INA is  $2.5\text{k}\Omega$ , because each input sees the parallel circuit of two bridge resistors.

The parallel resistance,  $R_P$ , of the reference buffer, contributing to thermal noise and voltage noise because noise current, is given with  $R_P = R_F = R_1 \parallel R_2 = 50\text{k}\Omega$ .

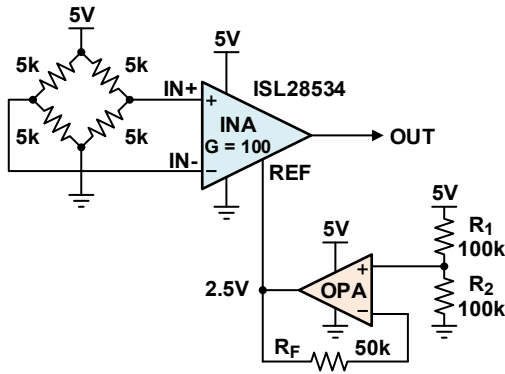


Figure 6. Signal Conditioner with INA ISL28534 at G = 100

INA		OPA	
G <sub>INA</sub>	100	G <sub>OPA</sub>	1
e <sub>n</sub> (INA)	18 nV/√Hz	e <sub>n</sub> (OPA)	10 nV/√Hz
i <sub>n</sub> (INA)	50 fA/√Hz	i <sub>n</sub> (OPA)	200 fA/√Hz
GBWP	2.3 MHz	GBWP	3.0 MHz
f <sub>BW</sub> (INA)	23 kHz	f <sub>BW</sub> (OPA)	3.0 MHz
NEB <sub>INA</sub>	36.1 kHz	NEB <sub>OPA</sub>	4.71 MHz
R <sub>S</sub> /2	2.5 kΩ	R <sub>P</sub> = R <sub>F</sub> = R <sub>1</sub>   R <sub>2</sub>	50 kΩ

Figure 7. Parametric Values of Signal Conditioner

### 3.1 INA Output Noise

Applying [Equation 3](#) gives the rms output noise of only the INA:

$$(EQ. 5) \quad E_{no(INA)} = G_{INA} \cdot \sqrt{NEB_{INA}} \cdot \sqrt{e_{n(INA)}^2 + 2 i_{n(INA)}^2 (R_S/2)^2} = 342 \mu V_{rms}$$

### 3.2 Thermal Noise due to Source Resistance

The thermal noise of each resistor is calculated with the following:

$$(EQ. 6) \quad E_{Rs/2} = \sqrt{4kT \cdot NEB_{INA} \cdot R_S/2}$$

where  $k = 1.38 \cdot 10^{-23}$  J/K is Boltzmann's constant, T is the absolute temperature in Kelvins, and R is the resistance in ohms. Since the input noise sources are uncorrelated, their total rms noise at the INA input is:

$$(EQ. 7) \quad E_{ni(Rs)} = \sqrt{E_{Rs/2}^2 + E_{Rs/2}^2} = \sqrt{2 \cdot E_{Rs/2}^2} = \sqrt{8kTR_S/2 \cdot NEB_{INA}}$$

This noise is amplified by the INA gain to produce an output noise of:

$$(EQ. 8) \quad E_{no(Rs)} = G_{INA} \cdot E_{ni(Rs)} = G_{INA} \cdot \sqrt{8kTR_S/2 \cdot NEB_{INA}} = 161 \mu V_{rms}$$

### 3.3 Output Noise of the Reference Buffer

The output noise of the voltage reference buffer is calculated, using [Equation 9](#). This equation is derived in Application Note: Noise Calculations of Op-AMP Circuits. Since the reference buffer operates at a gain of one, its output noise equals its input noise:

$$(EQ. 9) \quad E_{no(REF)} = E_{ni(REF)} = \sqrt{NEB_{OPA} \cdot \sqrt{8kTR_P + 2R_P^2 i_{n(OPA)}^2 + e_{n(OPA)}^2}} = 96 \mu V_{rms}$$

### 3.4 Total Circuit Output Noise

Now we can apply [Equation 4](#), which adds all three output noise components in rms fashion to yield the total rms output noise of the circuit:

$$(EQ. 10) \quad E_{no} = \sqrt{E_{no(INA)}^2 + E_{no(Rs)}^2 + E_{no(REF)}^2} = \sqrt{(342 \mu V)^2 + (161 \mu V)^2 + (96 \mu V)^2} = 390 \mu V$$

## 4. Conclusion

The dominant noise component is that of the INA. This noise can be reduced by drastically reducing the signal bandwidth through a low-pass filter at the INA output.

Further noise reduction is achieved by reducing the bandwidth of the bridge sensor. In this case, each INA input receives a low-pass filter.

Lastly, the noise of the reference buffer can be reduced by connecting a large input capacitor (10 $\mu$ F to 100 $\mu$ F) in parallel to  $R_2$  and a small feedback capacitor (10nF) in parallel to  $R_F$ . Using lower resistor values is also possible but comes at the cost of higher current consumption.

## 5. Revision History

Rev.	Date	Description
1.00	Aug.20.20	Initial release

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